

Silicon NPN Power Transistors

2N6355

DESCRIPTION

- With TO-3 package
- High DC current gain
- DARLINGTON

APPLICATIONS

- For general-purpose amplifier and low-frequency switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

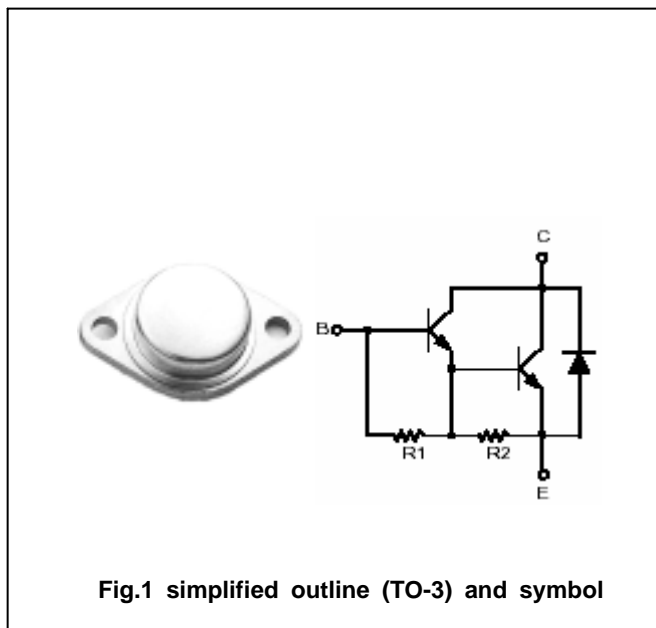


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	50	V
V _{CEO}	Collector-emitter voltage	Open base	40	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		20	A
I _B	Base current		0.5	A
P _D	Total Power Dissipation	T _C =25	150	W
T _j	Junction temperature		200	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.09	/W

Silicon NPN Power Transistors

2N6355

CHARACTERISTICS

 $T_j=25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=0.2A ; I_B=0$	40			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	$I_C=10A ; I_B=40mA$			2.0	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	$I_C=20A ; I_B=1A$			4.0	V
$V_{BE sat}$	Base-emitter saturation voltage	$I_C=20A ; I_B=1A$			4.0	V
V_{BE}	Base-emitter on voltage	$I_C=10A ; V_{CE}=4V$			2.8	V
I_{CEO}	Collector cut-off current	$V_{CE}=40V ; I_B=0$			1.0	mA
I_{CBO}	Collector cut-off current	$V_{CB}=50V ; I_E=0$			0.5	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			5.0	mA
h_{FE-1}	DC current gain	$I_C=4A ; V_{CE}=5V$	500		5000	
h_{FE-2}	DC current gain	$I_C=20A ; V_{CE}=5V$	100			

Silicon NPN Power Transistors

2N6355

PACKAGE OUTLINE

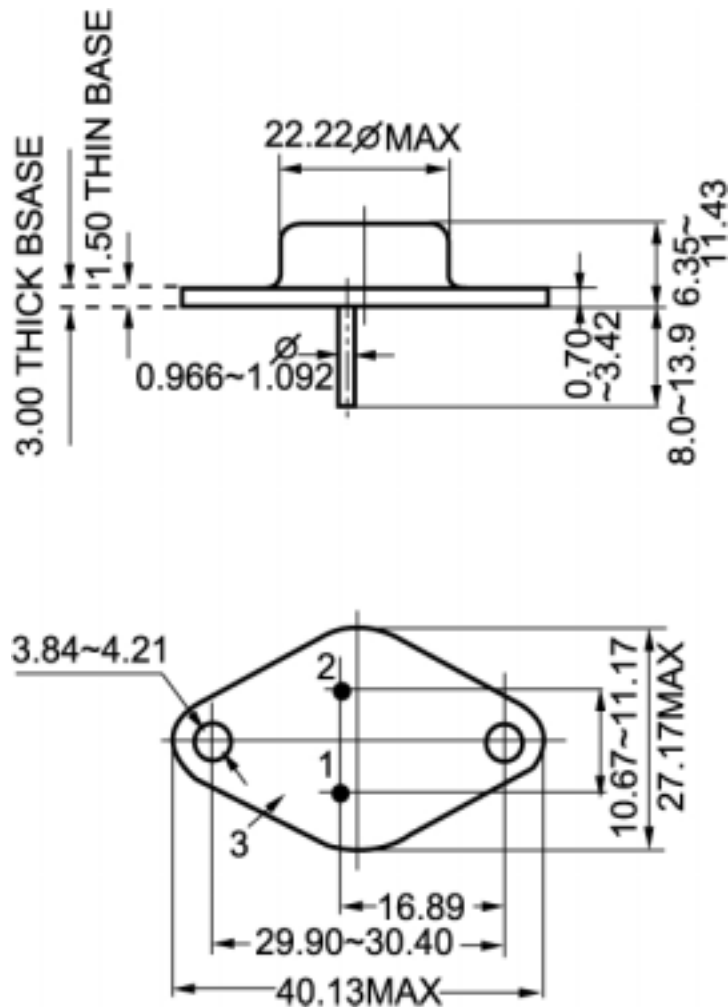


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.10\text{mm}$)